

N-channel TrenchMOS logic level FET

Rev. 02 — 9 March 2010

Product data sheet

Suitable for logic level gate drive

Switched-mode power supplies

sources

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

Simple gate drive required due to low gate charge

1.3 Applications

DC-to-DC convertors

1.4 Quick reference data

Table 1. Symbol Parameter Conditions Min Тур Max Unit T_i ≥ 25 °C; T_i ≤ 175 °C ٧ VDS drain-source voltage 30 _ _ drain current $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ 75 А I_D see Figure 1 and 3 **P**_{tot} total power dissipation T_{mb} = 25 °C; see Figure 2 120 W --**Dynamic characteristics** $V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ A};$ gate-drain charge 4.6 nC Q_{GD} _ V_{DS} = 15 V; T_i = 25 °C; see Figure 11 Static characteristics 10 R_{DSon} drain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ 8 mΩ -T_i = 25 °C; see Figure 9 resistance

Quick reference



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2. Pinning information

Table 2.	Pinning	information				
Pin	Symbol	Description		Simplified outline	Graphic symbol	
1	G	gate			_	
2	D	drain	<u>[1]</u>	mb		
3	S	source				
mb	D	mounting base; connected to drain			mbb076 S	
				SOT428 (DPAK)		

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package				
	Name	Description	Version		
PHD71NQ03LT	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

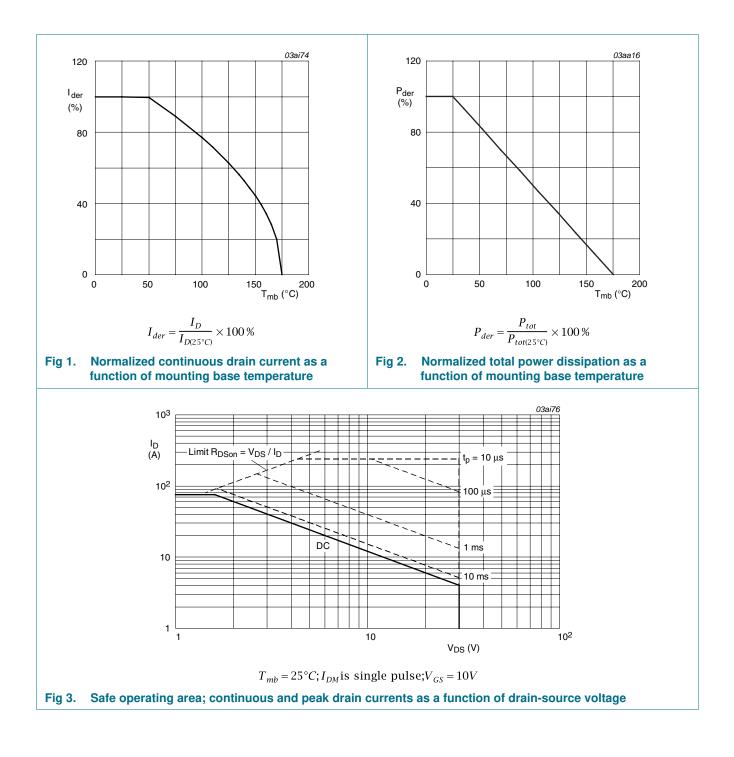
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	57.5	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> and <u>3</u>	-	75	А
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	240	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	120	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V_{GSM}	peak gate-source voltage	pulsed; δ = 25 %; t_p ≤ 50 μs	-25	25	V
Source-di	rain diode				
I _S	source current	T _{mb} = 25 °C	-	75	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	57.7	А

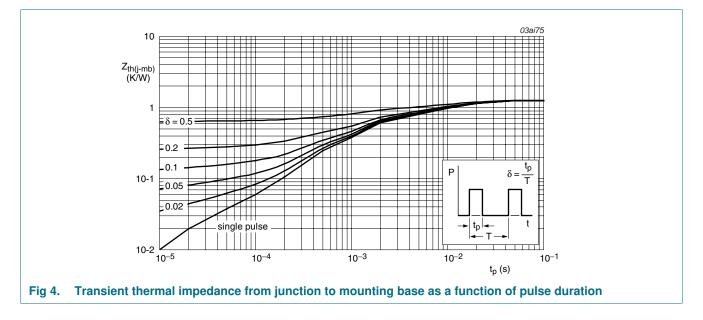
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.25	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	75	-	K/W

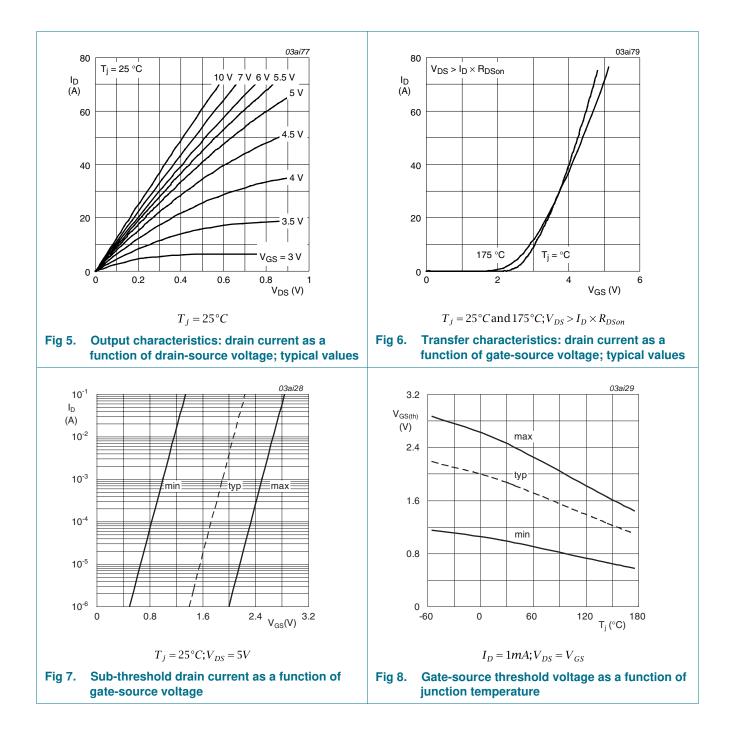


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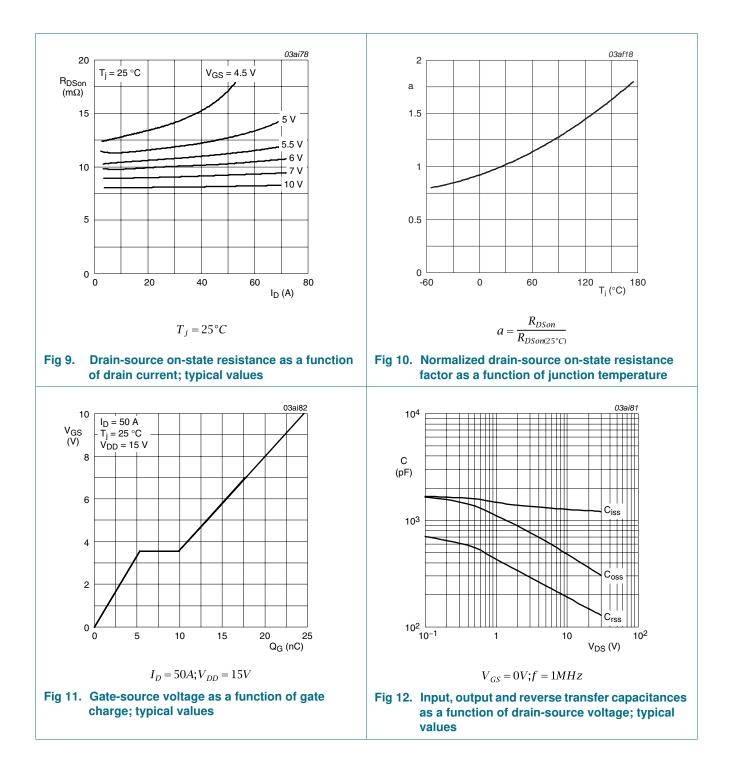
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	27	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	30	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{see } \frac{\text{Figure 8}}{1000 \text{ Figure 8}}$	0.6	-	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } \frac{\text{Figure 8}}{\text{Figure 8}}$	-	-	2.9	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure 8}}{1000 \text{ Figure 8}}$	1	1.9	2.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 5 V; I_{D} = 25 A; T_{j} = 175 °C; see Figure 9 and $\underline{10}$	-	21.6	27.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 9</u>	-	8	10	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 9</u> and <u>10</u>	-	12	15.2	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 50 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ °C};$	-	13.2	-	nC
Q _{GS}	gate-source charge	see <u>Figure 11</u>		5.3	-	nC
Q _{GD}	gate-drain charge		-	4.6	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$	-	1220	-	pF
C _{oss}	output capacitance	see Figure 12	-	330	-	pF
C _{rss}	reverse transfer capacitance		-	140	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω; V_{GS} = 4.5 V;	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; T_j = 25 \ ^{\circ}C; I_D = 25 \ A$	-	150	-	ns
t _{d(off)}	turn-off delay time		-	13.5	-	ns
t _f	fall time		-	18	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	-	0.9	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	29	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	20	-	nC

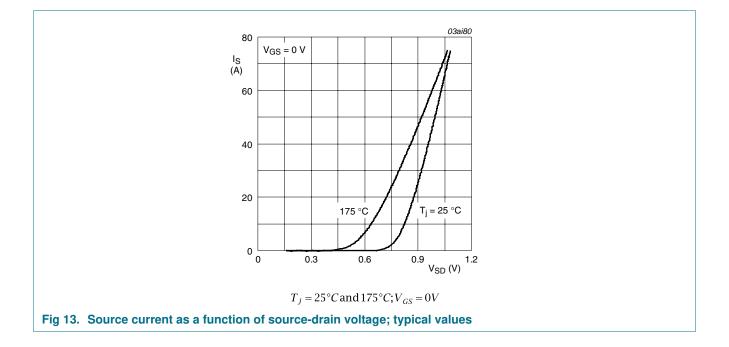
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7. Package outline

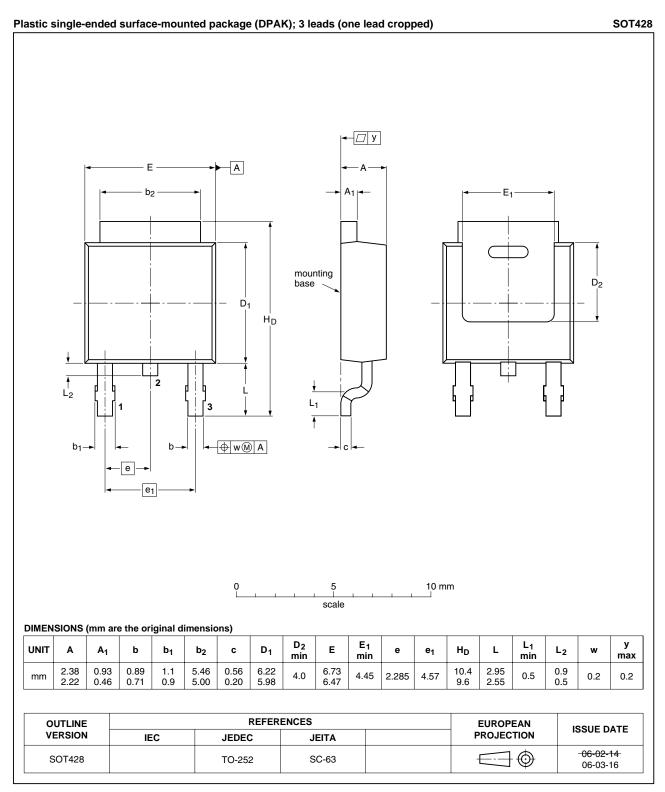


Fig 14. Package outline SOT428 (DPAK)

PHD71NQ03LT_2 Product data sheet

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8. Revision history

Table 7.Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
PHD71NQ03LT_2	20100309	Product data sheet	-	PHP_PHB_PHD71NQ03LT-01		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts 	have been adapted to	the new company	name where appropriate.		
		per PHD71NQ03LT sep _PHD71NQ03LT-01.	parated from data s	heet		
PHP_PHB_PHD71NQ03LT-01	20020625	Product data	-	-		

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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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